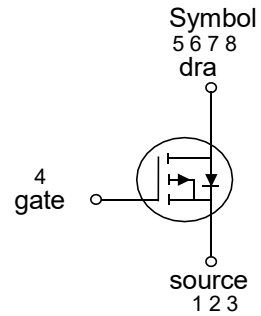


■ PRODUCT CHARACTERISTICS

V_{DSS}	-40V
$R_{DS(on)}$ Typ(@ $V_{GS}=-10V$)	20m Ω
$R_{DS(on)}$ Typ(@ $V_{GS}=-4.5V$)	29m Ω
I_D	-15A

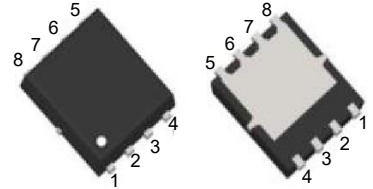


■ APPLICATIONS

- PWM applications
- Load switch
- Power management

■ FEATURES

- High power and current handling capability
- Lead free product is required
- Surface mount package



PDFN3X3



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MOT4733J	PDFN3X3	5000pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DSS}	-40	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current(@ $V_{GS}=-10V$, $T_A=25^{\circ}C$)	I_D	-15	A
Pulsed drain current	I_{DM}	-60	A
Power dissipation	P_D	25	W
Junction temperature	T_J	+150	$^{\circ}C$
Storage temperature	T_{STG}	-55~ +150	$^{\circ}C$

■ THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	5	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C$, $V_{DD}=20V$, $V_G=10V$, $L=0.5mH$, $R_g=25\Omega$

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250μA	-40	-	-	V
Drain-source leakage current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1	μA
Gate-source leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	100	nA
On characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.2	-1.6	-2.5	V
On-state characteristics	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-10A	-	29	35	mΩ
		V _{GS} =-10V, I _D =-10A	-	20	25	mΩ
Forward transconductance	g _{FS}	V _{DS} =10V, I _D =-3A	-	8	-	S
Dynamic characteristics						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-20V f=1MHz	-	928	-	pF
Out capacitance	C _{oss}		-	133	-	pF
Reverse transfer capacitance	C _{rss}		-	89	-	pF
Switching characteristics						
Total gate charge	Q _g	V _{GS} =-10V, V _{DS} =-20V I _D =-15A	-	23	-	nC
Gate-source charge	Q _{gs}		-	2.2	-	nC
Gate-drain charge	Q _{gd}		-	6.5	-	nC
Turn-on delay time	t _{d(on)}	V _{DS} =-20V, I _D =-15A R _G =3Ω, V _{GS} =-10V	-	11	-	nS
Turn-on rise time	t _r		-	11	-	nS
Turn-off delay time	t _{d(off)}		-	35	-	nS
Turn-off fall time	t _f		-	15	-	nS
Source-drain diode ratings and characteristics						
Continuous diode forward current	I _{SD}		-	-	-15	A
Diode forward current	V _{SD}	V _{GS} =0V, I _{SD} =-1A	-	-0.79	-1.2	V

■ TYPICAL CHARACTERISTICS

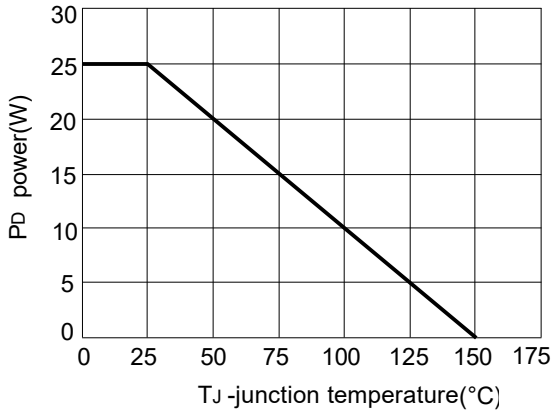


Fig.1 power dissipation

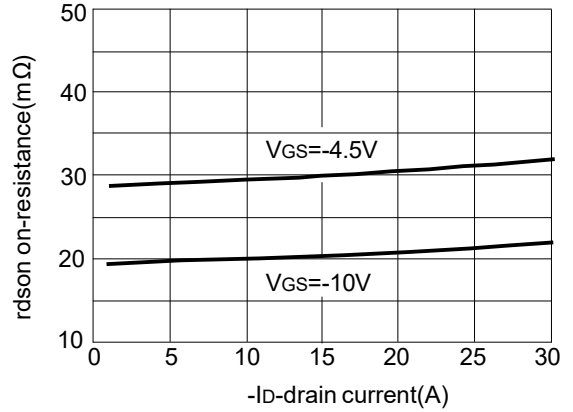


Fig.2 drain-source on-resistance

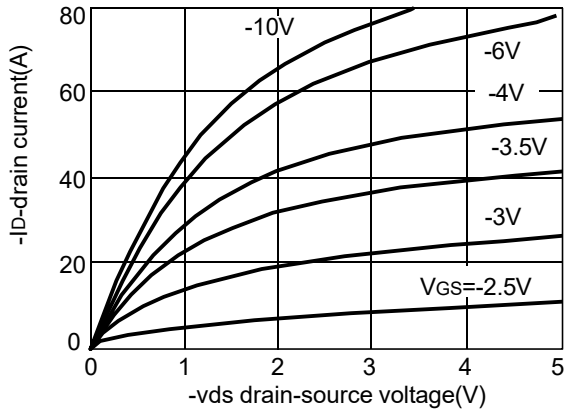


Fig.3 output characteristics

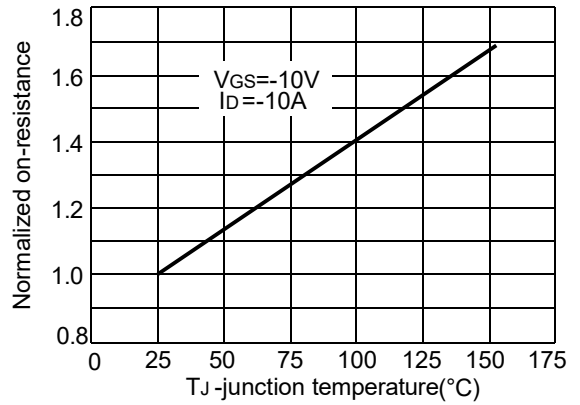


Fig.4 drain-source on-resistance

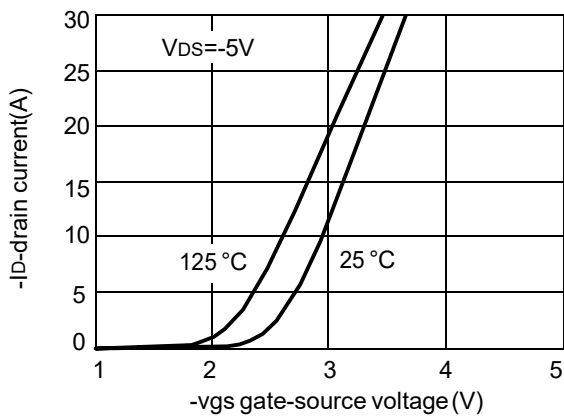


Fig.5 transfer characteristics

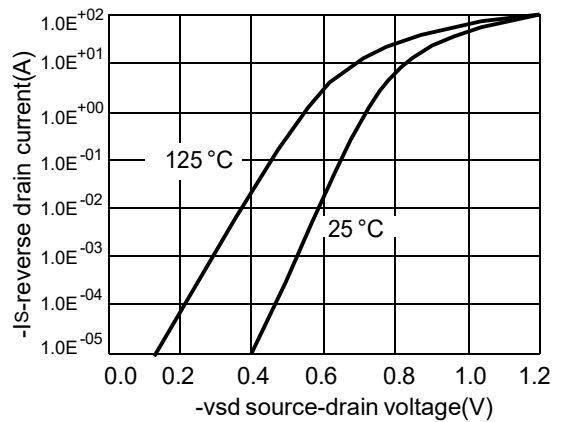


Fig.6 source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

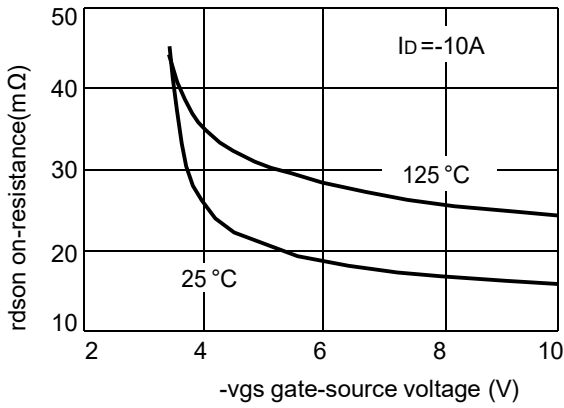


Fig.7 rdson vs vgs

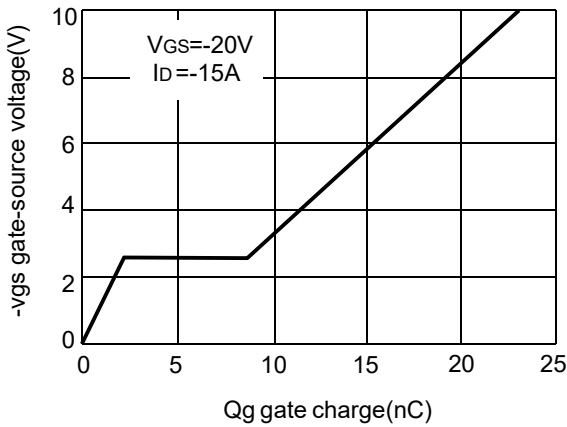


Fig.9 gate charge

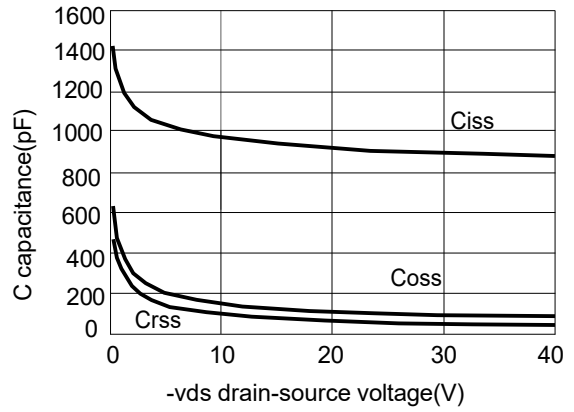


Fig.8 capacitance vs vds

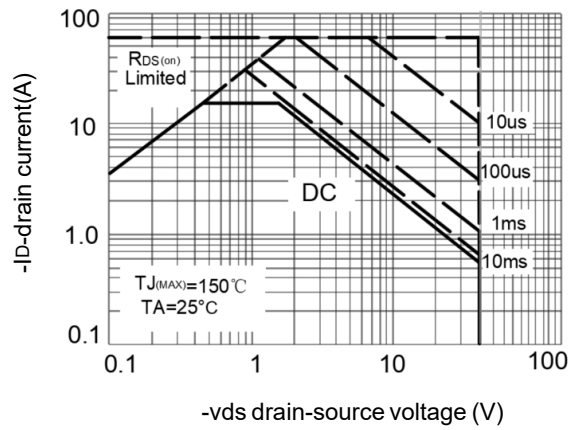
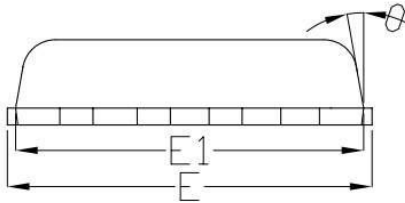
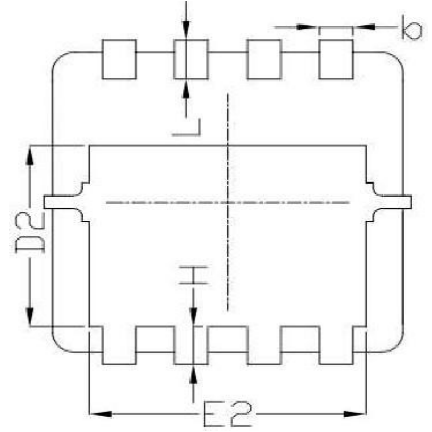
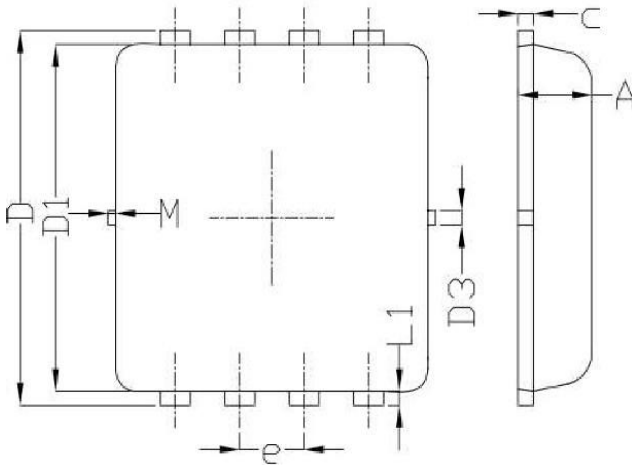
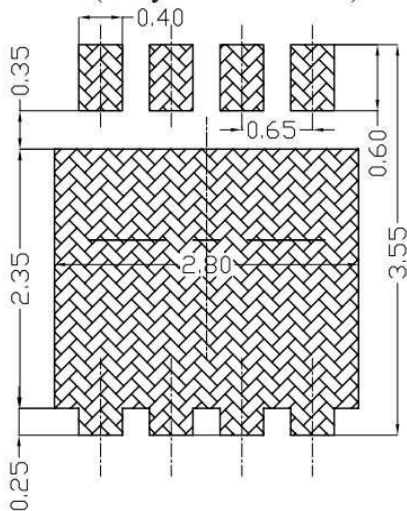


Fig.10 safe operation area

■ PDFN3X3 PACKAGE MECHANICAL DATA



Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			